



Low forward voltage Transil™, transient voltage suppressor

Datasheet - production data

Features

- Strong ESD and EOS protection
- Very low clamping factor V_{CL}/V_{BR}
- Unidirectional device
- Fast response time
- Very thin package
- Very small PCB area
- RoHS compliant

Complies with the following standards:

- IEC 61000-4-2 level 4
 - ±15 kV (air discharge)
 - ±8 kV (contact discharge)

Description

The LFTVS18-1F3 is a single line diode designed specifically for the protection of integrated circuits in portable equipment and miniaturized electronics devices subject to ESD and EOS transient overvoltages.

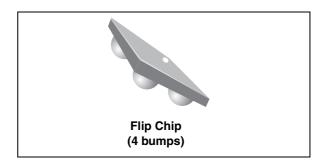


Figure 1. Pin configuration (bump side)

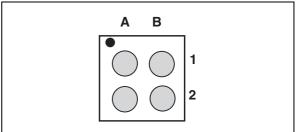
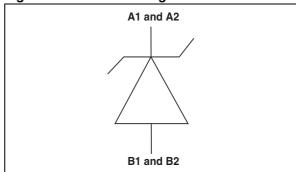


Figure 2. Device configuration



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Characteristics LFTVS18-1F3

1 Characteristics

Table 1. Absolute maximum ratings ($T_{amb} = 25$ °C)

Symbol	Parameter	Test condition	Value	Unit
P _{PP}	Peak pulse power dissipation (8/20 µs pulse)	T _j initial = T _{amb}	350	W
I _{FSM}	Non repetitive surge peak forward current	$t_p = 10 \text{ ms}, T_j \text{ initial} = T_{amb}$	5	Α
T _j	Maximum operating junction temperature		125	°C
T _{stg}	Storage temperature range		-55 to +150	°C

Figure 3. Electrical characteristics - definitions

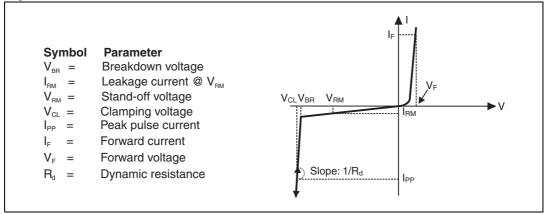


Table 2. Electrical characteristics - values ($T_{amb} = 25$ °C)

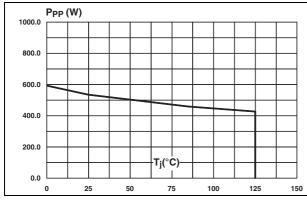
Symbol	Test conditions	Min.	Тур.	Max.	Unit
V_{BR}	I _R = 1 mA	16			V
I _{RM}	V _{RM} = 12 V			250	nA
V _{CL}	$I_{PP} = 1 A^{(1)}$			19	V
V _F	I _F = 850 mA			1.3	V
C _{line}	$V_R = 0 \text{ V}, V_{OSC} = 30 \text{ mV}, F = 1 \text{ MHz}$		175		pF

^{1. 8 / 20} µs pulse waveform

LFTVS18-1F3 Characteristics

Figure 4. Peak pulse power versus initial junction temperature (pulse 8/20 µs)

Figure 5. Peak pulse power versus initial junction temperature (pulse 10/1000 μs)



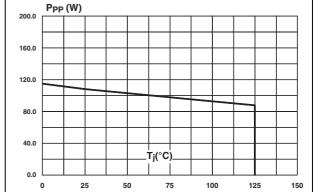
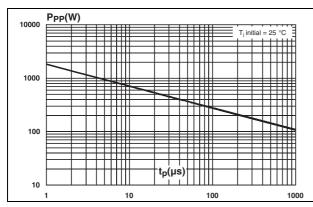


Figure 6. Peak pulse power versus exponential pulse duration

Figure 7. Clamping voltage versus peak pulse current (8/20 μs, typical values)



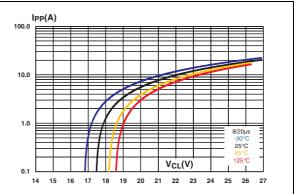
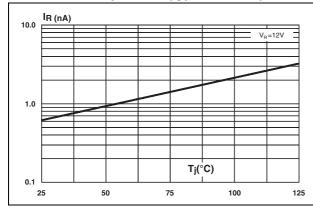
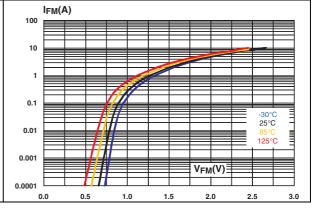


Figure 8. Leakage current versus junction temperature (typical values)

Figure 9. Forward voltage drop versus peak forward current (typical values)

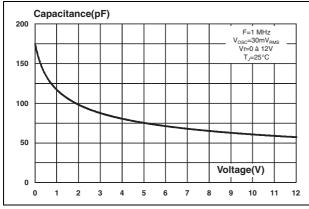




Characteristics LFTVS18-1F3

Figure 10. Junction capacitance versus line voltage (typical values)

Figure 11. Junction capacitance versus frequency for different bias voltages (P = -12 dBm)



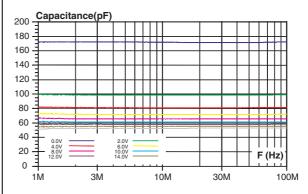
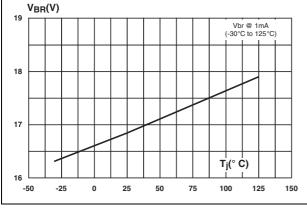


Figure 12. Breakdown voltage versus initial junction temperature (typical value)

Figure 13. S21 insertion losses versus frequency response



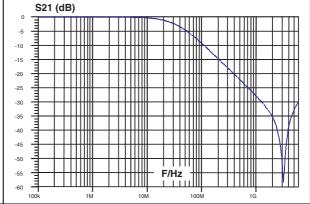
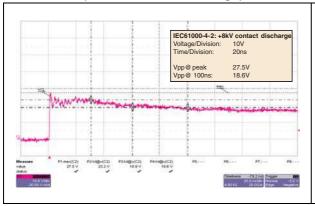
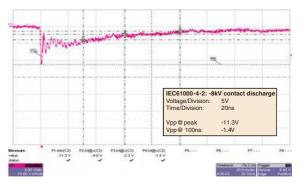


Figure 14. ESD response to IEC 61000-4-2 (+8 kV contact discharge)

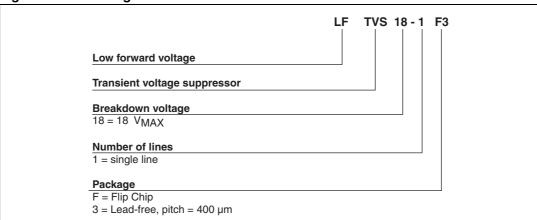
Figure 15. ESD response to IEC 61000-4-2 (-8 kV contact discharge)





2 Ordering information scheme

Figure 16. Ordering information scheme



Package information LFTVS18-1F3

3 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 17. Package dimensions

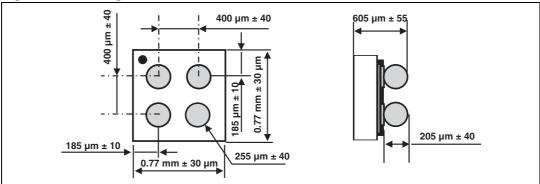
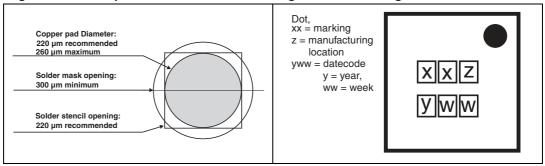


Figure 18. Foot print recommendations Figure 19. Marking



Note:

Product marking may be rotated by 90° for assembly plant differentiation. In no case should this product marking be used to orient the component for its placement on a PCB. Only pin 1 mark is to be used for this purpose.

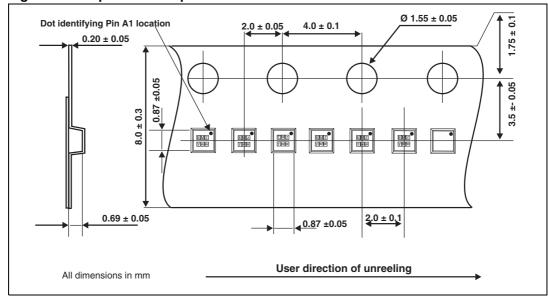


Figure 20. Tape and reel specifications

Note:

More information is available in the Application notes:

AN2348: "400 μm Flip Chip: package description and recommendations for use"

AN1751: "EMI Filters: recommendations and measurements"

4 Ordering information

Table 3. Ordering information

Order code	Marking ⁽¹⁾	Package	Weight	Base qty	Delivery mode
LFTVS18-1F3	EM	Flip Chip	0.79 mg	10 000	Tape and reel (7")

^{1.} The marking can be rotated by 90° to differentiate assembly location

5 Revision history

Table 4. Document revision history

Date	Revision	Changes
06-Mar-2008	1	Initial release.
04-Sep-2008	2	Updated V_F to 1.05 V. Updated <i>Figure 20</i> to show pitch of 2.0 mm. Updated I_{FSM} to 11 A. Updated <i>Figure 5</i> , <i>Figure 7</i> , and <i>Figure 8</i> .
14-Sep-2012	3	Updated all graphics in 1: Characteristics. Added tolerances to pocket dimensions in Figure 20.

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